


GaN on SiC HEMT Pulsed Power Transistor
250W Peak, 960-1215 MHz, 128μs Pulse, 10% Duty
Production V1
18 Aug 11
Features

- GaN depletion mode HEMT microwave transistor
- Internally matched
- Common source configuration
- Broadband Class AB operation
- RoHS Compliant
- +50V Typical Operation
- MTTF of 114 years (Channel Temperature < 200°C)

Applications

- Avionics: Mode-S, TCAS, JTIDS, DME and TACAN.

Product Description

The MAGX-000912-250L00 is a gold metalized matched Gallium Nitride (GaN) on Silicon Carbide RF power transistor optimized for civilian and military pulsed avionics amplifier applications the 960 MHz to 1215 MHz range such as Mode-S, TCAS, JTIDS, DME and TACAN . Using state of the art wafer fabrication processes, these high performance transistors provide high gain, efficiency, bandwidth, ruggedness over a wide bandwidth for today's demanding application needs. High breakdown voltages allow for reliable and stable operation in extreme mismatched load conditions unparalleled with older semiconductor technologies.


Typical RF Performance at Pout = 250W Peak

Freq (MHz)	Pin (W)	Gain (dB)	Slope (dB)	Id (A)	Eff (%)	Avg-Eff (%)	RL (dB)	Droop (dB)
960	3.4	18.7	-	8.5	58.8	-	-8.8	0.4
1030	4.2	17.8	-	8.3	60.1	-	-12.7	0.4
1090	3.4	18.7	-	8.2	61.1	-	-9.3	0.4
1150	3.4	18.7	-	8.2	60.7	-	-8.6	0.3
1215	3.5	18.6	1.0	8.6	58.0	59.7	-11.5	0.4

Ordering Information

MAGX-000912-250L00 250W GaN Power Transistor
 MAGX-000912-SB1PPR Evaluation Fixture

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Absolute Maximum Ratings Table (1, 2, 3)

Supply Voltage (V_{DD})	+65V
Supply Voltage (V_{GS})	-8 to -2V
Supply Current ($I_{D_{MAX}}$)	14.2 Apk
Input Power (P_{IN})	+40 dBm
Absolute Max. Junction/Channel Temp	200 °C
MTTF ($T_J < 200^\circ\text{C}$)	114 years
Pulsed Power Dissipation at 85°C	460 Wpk
Thermal Resistance, ($T_J = 70^\circ\text{C}$) $V_{DD} = 50\text{V}$, $I_{DQ} = 250\text{mA}$, $P_{out} = 250\text{W}$ 128 μ s Pulse / 10% Duty	0.25°C/W
Operating Temp	-40 to +95°C
Storage Temp	-65 to +150°C
Mounting Temperature	See solder reflow profile
ESD Min. - Machine Model (MM)	50V
ESD Min. - Human Body Model (HBM)	>250V
MSL Level	MSL1

(1) Operation of this device above any one of these parameters may cause permanent damage.

(2) Channel temperature directly affects a device's MTTF. Channel temperature should be kept as low as possible to maximize lifetime.

(3) For saturated performance it recommended that the sum of ($3 \cdot V_{dd} + \text{abs}(V_{gg})$) < 175

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
DC CHARACTERISTICS						
Drain-Source Leakage Current	$V_{GS} = -8\text{V}$, $V_{DS} = 175\text{V}$	I_{DS}	-	0.4	12	mA
Gate Threshold Voltage	$V_{DS} = 5\text{V}$, $I_D = 30\text{mA}$	$V_{GS(th)}$	-5	-3.1	-2	V
Forward Transconductance	$V_{DS} = 5\text{V}$, $I_D = 7.0\text{mA}$	G_M	5.0	7.7	-	S
DYNAMIC CHARACTERISTICS						
Input Capacitance	Not applicable—Input internally matched	C_{ISS}	N/A	N/A	N/A	pF
Output Capacitance	$V_{DS} = 50\text{V}$, $V_{GS} = -8\text{V}$, $F = 1\text{MHz}$	C_{OSS}	-	22	-	pF
Feedback Capacitance	$V_{DS} = 50\text{V}$, $V_{GS} = -8\text{V}$, $F = 1\text{MHz}$	C_{RSS}	-	2.2	-	pF

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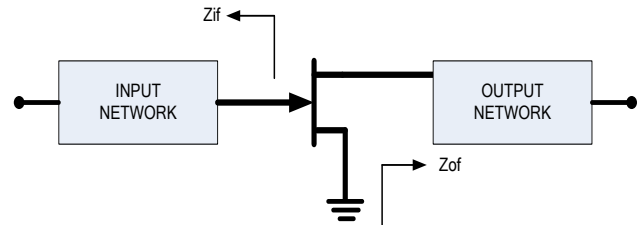
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Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
RF FUNCTIONAL TESTS ($V_{DD} = 50\text{V}$, $I_{DQ} = 250\text{mA}$, 128μs / 10% duty, 960-1215MHz)						
Input Power	$P_{out} = 250\text{W Peak (25W avg)}$	P_{IN}	-	3.5	5.3	Wpk
Power Gain	$P_{out} = 250\text{W Peak (25W avg)}$	G_P	16.7	18.5	-	dB
Drain Efficiency	$P_{out} = 250\text{W Peak (25W avg)}$	η_D	52	59.7	-	%
Load Mismatch Stability	$P_{out} = 250\text{W Peak (25W avg)}$	VSWR-S	5:1	-	-	-
Load Mismatch Tolerance	$P_{out} = 250\text{W Peak (25W avg)}$	VSWR-T	10:1	-	-	-

Test Fixture Impedance

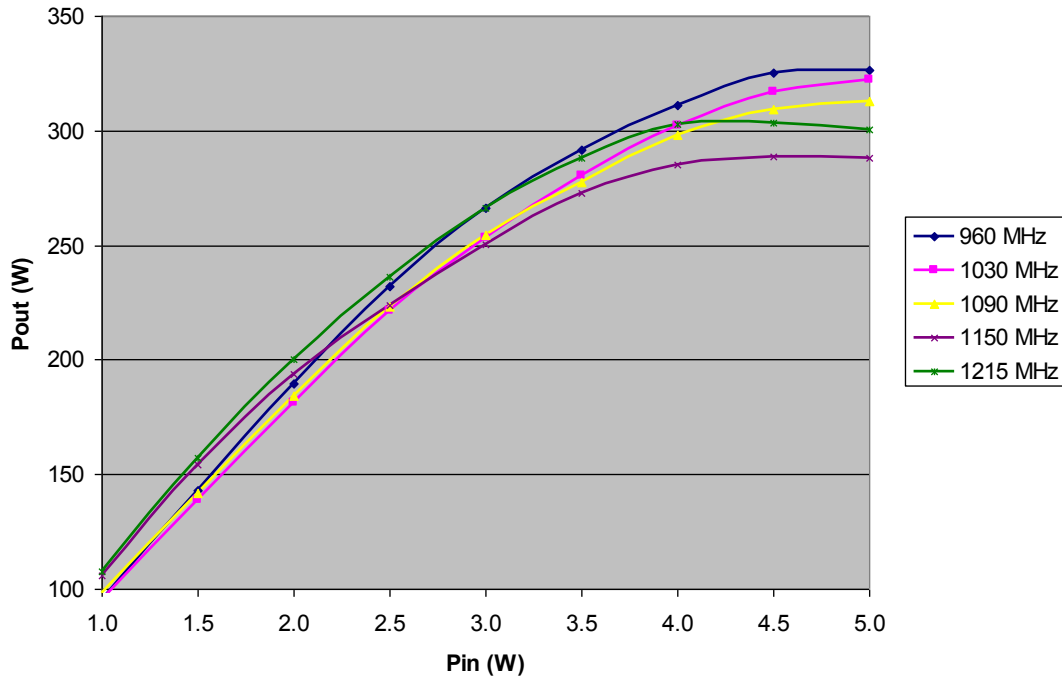
F (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
960	2.6 - j4.6	4.0 + j0.0
1030	2.8 - j3.6	3.7 - j0.4
1090	2.8 - j3.9	3.6 - j0.4
1150	2.7 - j3.5	3.5 - j0.4
1215	2.8 - j3.1	3.6 - j0.5



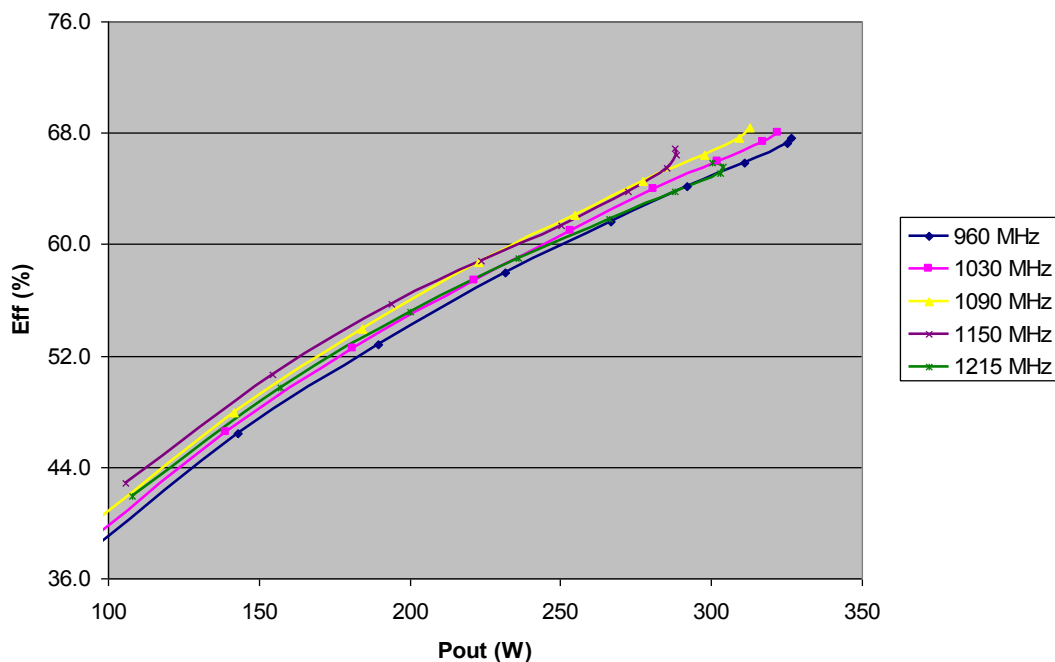
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RF Power Transfer Curve (Output Power Vs. Input Power)



RF Power Transfer Curve (Drain Efficiency Vs. Output Power)



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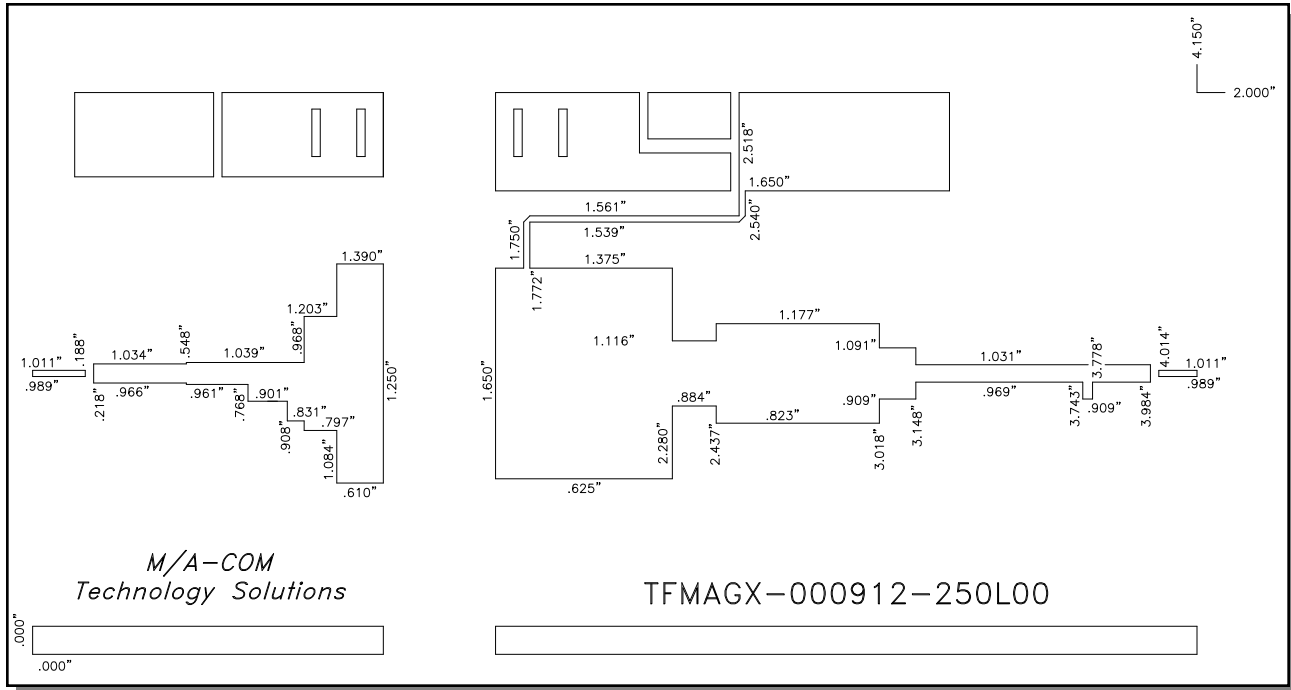
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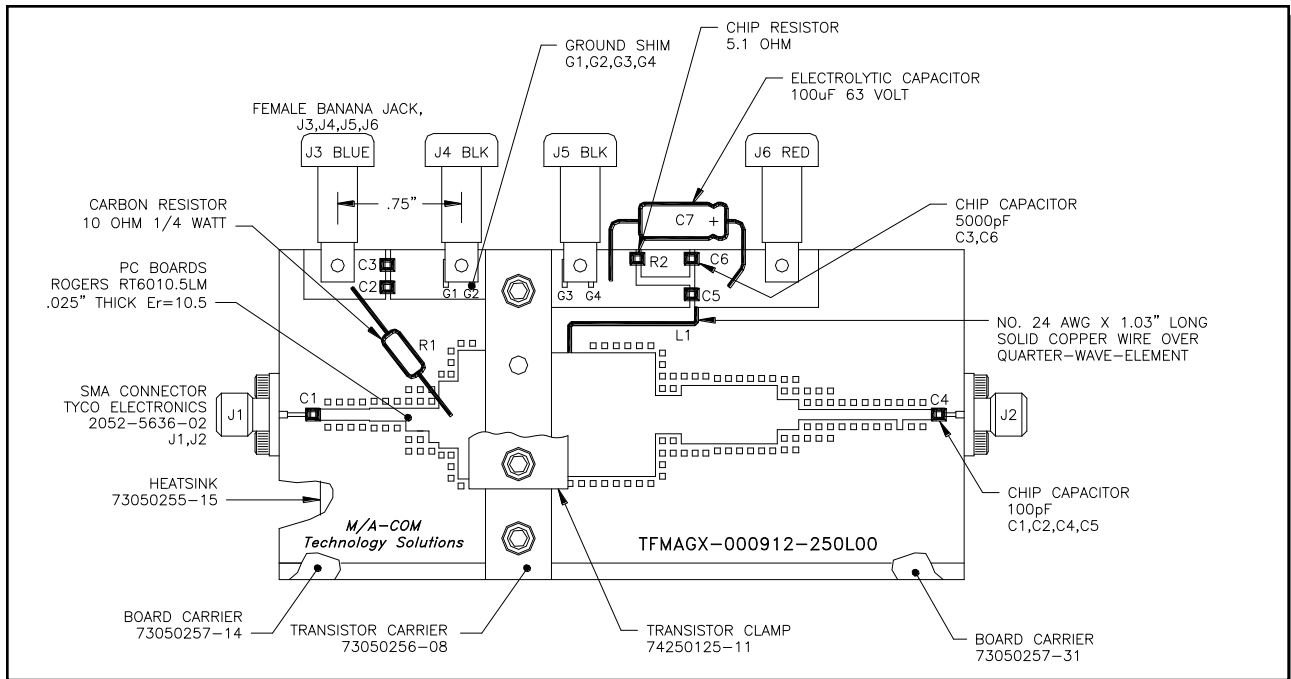
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Test Fixture Circuit Dimensions



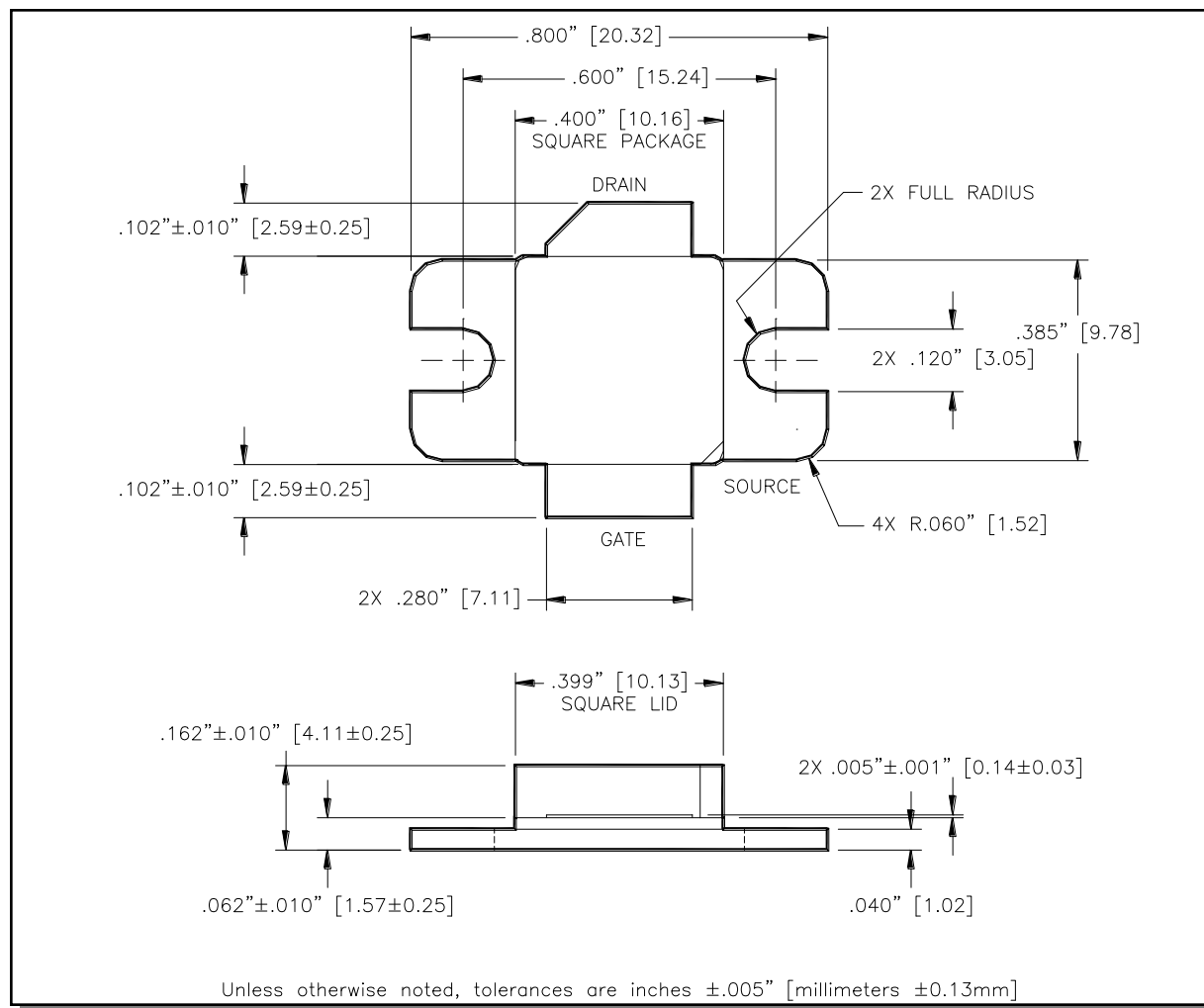
Test Fixture Assembly



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Outline Drawing



CORRECT DEVICE SEQUENCING

TURNING THE DEVICE ON

1. Set V_{GS} to the pinch-off (V_P), typically -5V
2. Turn on V_{DS} to nominal voltage (50V)
3. Increase V_{GS} until the I_{DS} current is reached
4. Apply RF power to desired level

TURNING THE DEVICE OFF

1. Turn the RF power off
2. Decrease V_{GS} down to V_P
3. Decrease V_{DS} down to 0V
4. Turn off V_{GS}